

## 产品概览

### NTMFS4983NF: 单 N 沟道，功率 MOSFET，30V，106A，2.1mΩ

欲看完整文档，请参阅数据表。

功率 MOSFET，30 V，106 A，单 N 沟道，SO-8 FL

### 特性

- Integrated Schottky Diode
- Low rDS(on) to Minimize Conduction Loss
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- RoHS Compliant

### 应用

- CPU Power Delivery
- Synchronous Rectification for DC-DC Converters
- Low Side Switching
- Telecom Secondary Side Rectification

### 器件电气规格

产品	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DS(s)}$ Min (V)	$V_{GS}$ Max (V)	$V_{GS(th)}$ Max (V)	$I_D$ Max (A)	$P_D$ Max (W)	$R_{DS(on)}$ Max @ $V_{GS} = 2.5V$ (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 4.5V$ (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 10V$ (mΩ)	$Q_g$ Typ @ $V_{GS} = 4.5V$ (nC)	$Q_g$ Typ @ $V_{GS} = 10V$ (nC)	$C_{iss}$ Typ (pF)	Package Type
NTMFS4983NFT1G	0.4	Pb-free Halide free non AEC-Q and PPAP	Active	N-Channel	Single	30	20	2.3	106	3.13	-	3.1	2.1	25	22.6	3250	SO-8FL / DFN-5
NTMFS4983NFT3G	0.4009	Pb-free Halide free non AEC-Q and PPAP	Active	N-Channel	Single	30	20	2.3	106	3.13	-	3.1	2.1	25	22.6	3250	SO-8FL / DFN-5

欲了解更多信息，请联系您当地的销售支援 [www.onsemi.cn](http://www.onsemi.cn)。

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